

# 7.5V to 15V, 2A Integrated MOSFET 1ch Synchronous Buck DC/DC Converter



## Free RoHS

0.8V to 5.5V

2.0A (Max.)

# **BD95821MUV**

#### Description

BD95821MUV is a 1ch synchronous buck converter that can generate output voltage (0.8V to 5.5V) at the input voltage range (7.5V to 15V). Space-saving and high efficient switching regulator can be achieved due to built-in N-MOSFET power transistors. The IC also incorporates  $H^3 Reg^{TM}$  technology, a Rohm proprietary constant ON TIME control mode which facilitates ultra-high transient response against changes in load without external compensation components. Fixed soft start function, power good function, and short circuit / over voltage protection with timer latch functions are incorporated. The BD95821MUV is designed for power supplies for Digital AV Equipment.

#### Applications

- LCD TVs
- · Set Top Boxes (STB)
- · DVD/Blu-ray players/recorders
- · Broadband Network and Communication Interface
- · Amusement. other.

#### Features

- · Input Voltage Range: 7.5V to 15.0V
- Reference Voltage: 0.8V±1.5%
- Output Voltage Range:
- Output Current:
- · Switching Frequency:
- 500kHz to 800kHz (depend on input-output condition)
- Built-in Power MOS FET High-side Nch FET ON resistance: 120m Ω (typ.) Low-side Nch FET ON resistance:  $65m \Omega$  (typ.)
- Fast Transient Responses due to H<sup>3</sup>Reg control
- Over Current Protection (OCP) Cycle-by-Cycle
- Thermal Shut Down (TSD)
- Under-Voltage Lock-Out (UVLO)
- Short Circuit Protection (SCP)
- Over Voltage Protection (OVP)
- Fixed Soft Start (1msec ; typ)
- · Power Good function

VQFN016V3030

#### Package

W(Typ.) x D(Typ.) x H(Max.) 3.0mm x 3.0mm x 1.0mm

## Typical Application

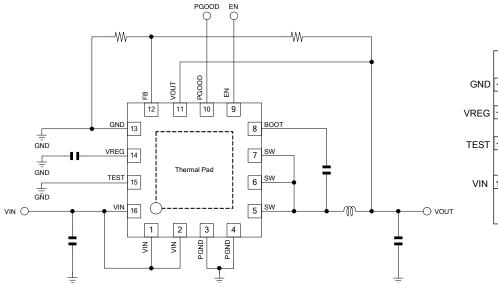
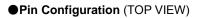
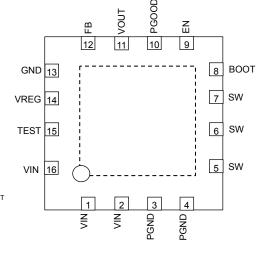
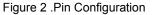


Figure 1. Typical Application Circuit







OProduct structure : Silicon monolithic integrated circuit OThis product is not designed protection against radioactive rays.

#### Block Diagram

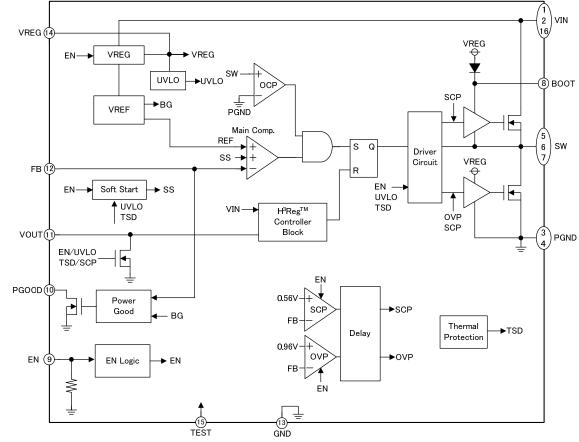


Figure 3. Block Diagram

#### Pin Description

No.	Symbol	Description
1, 2, 16	VIN	Input Voltage Supply pin. The IC determines the duty cycles internally based on the input voltage. Therefore, variations of VIN pin can lead to unstable operation. This pin also acts as the input voltage to the internal switching regulator output block, and is sensitive to the impedance of the power supply. Connect over $10\mu$ F ceramic capacitors for the decoupling capacitors to PGND as near as these pins.
3, 4	PGND	Power ground pin connected to the source of the Low side FET.
5, 6, 7	SW	Switch node connection between High side FET source and Low side FET drain. Connect $0.01\mu$ F capacitor between BOOT and SW. This pin is also connected to inductor (L).
8	BOOT	High side FET Gate Driver Power Supply pin. Connect 0.01μF capacitor between BOOT and SW. BOOT voltage swings from VREG to (VIN + VREG) during normal switching operation.
9	EN	Enable Input pin. When the input voltage of the EN pin reaches at least 2.2V, the switching regulator becomes active. At the voltage less than 0.3 V, the IC becomes standby mode.
10	PGOOD	Open-drain Power Good Output pin. Due to the open-drain output, a 100k $\Omega$ pull-up resistor should be connected between this pin and VREG or other power supply. In the case of no use, this pin is opened or shortened to ground.

## **BD95821MUV**

## Pin Description (Continued)

No.	Symbol	Description
11	VOUT	Output Voltage Sense pin. Connect to output voltage directly. ONTIME is determined by monitoring the output voltage.
12	FB	Output Voltage Feedback pin. FB is compared with REF in the IC. Please set the output voltage in the feedback resistances of less than total $50k\Omega$ . (Refer to page 15)
13	GND	Sense ground pin for all internal analog and digital power supplies.
14	VREG	Power supply output inside IC. When at least 2.2V is supplied to the EN pin, the VREG is active. This pin supplies 5.0V at up to 10mA. Insert a $0.022\mu$ F capacitor between this pin and ground pin.
15	TEST	TEST Pin. Connect to ground.
Thermal Pad	-	Exposed Thermal Pad. Connect to ground.

#### ● Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit	Comment
Input Voltage	VIN	15.2 * <sup>1</sup>	V	
BOOT Voltage	BOOT	21.5 * <sup>1</sup>	V	
BOOT-SW Voltage	BOOT-SW	7 * <sup>1</sup>	V	
Output Voltage	VOUT	7 * <sup>1</sup>	V	
SW Voltage	SW	15.2 * <sup>1</sup>	V	
Output Feedback Voltage	FB	VREG	V	
VREG Voltage	VREG	7 * <sup>1</sup>	V	
EN Input Voltage	EN	15.2 * <sup>1</sup>	V	
PGOOD Voltage	PGOOD	7 * <sup>1</sup>	V	
Power Dissipation 1	Pd1	0.27	W	Ta≧25°C (IC only), power dissipated at 2.2mW / °C.
Power Dissipation 2	Pd2	0.62	W	Ta≧25°C (70mm×70mm×1.6mm single-layer board, 6.28mm <sup>2</sup> copper heat dissipation pad), power dissipated at 5.0mW / °C.
Power Dissipation 3	Pd3	1.77	w	Ta $\geq 25^{\circ}$ C (70mm × 70mm × 1.6mm 4-layer board, 6.28 mm <sup>2</sup> copper heat dissipation pad on top and bottom layer, 5505 mm <sup>2</sup> pad on 2 <sup>nd</sup> and 3 <sup>rd</sup> layer), power dissipated at 14.1mW /°C.
Power Dissipation 4	Pd4	2.66	W	Ta≧25°C (70mm × 70mm × 1.6mm 4-layer board, all layers with 5505 mm <sup>2</sup> copper heat dissipation pads), power dissipated at 21.3mW / °C.
Operating Temperature Range	Topr	-20 to +100 * <sup>1</sup>	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	
Junction Temperature *1 Not to exceed Pd.	Tjmax	+150	°C	

\*1 Not to exceed Pd.

## ●Operating Ratings (Ta= -20 to 100°C)

Parameter	Symbol		Limit	Unit	
Falametei	Symbol	Min	Тур	Max	Unit
Input Voltage	VIN	7.5	12	15	V
VREG Voltage	VREG	4.5	5.0	5.5	V
BOOT Voltage	BOOT	4.5	-	21	V
SW Voltage	SW	-0.7	-	15	V
BOOT-SW Voltage	BOOT-SW	4.5	-	5.5	V
EN Input Voltage	EN	0	-	15	V
Output Voltage	VOUT <sup>*2</sup>	0.8	-	5.5	V
PGOOD Voltage	PGOOD	0	-	5.5	V
Minimum ON Time	Tonmin	-	-	200	nsec

 $^{\ast}2$  VOUT depends on Input Voltage (VIN) in some cases.

## •Electrical Characteristics

(Unless otherwise noted Ta=25°C, VIN=12V, EN=3V, VOUT=3.3V)

		<u>11-07, 700</u>	Limit			Condition
Parameter	Symbol	Min	Тур	Max	- Unit	
VIN Bias Current	l <sub>in</sub>	-	1.2	2.0	mA	
VIN Standby Current	I <sub>IN_STB</sub>	-	2	15	μA	EN=0V
Enable Control						
EN Low Voltage	EN <sub>LOW</sub>	GND	-	0.3	V	
EN High Voltage	EN <sub>HIGH</sub>	2.2	-	15	V	
EN Bias Current	I <sub>EN</sub>	-	3	10	μA	EN=3V
VREG Output Voltage						
VREG Standby Voltage	$V_{\text{REG}_{\text{STB}}}$	-	-	0.1	V	EN=0V
VREG Output Voltage	$V_{REG}$	4.5	5.0	5.5	V	I <sub>REG</sub> =10mA
Maximum Output Current	I <sub>REG</sub>	10	-	-	mA	
Power MOSFET						
High side FET ON Resistance	R <sub>ONH</sub>	-	120	240	mΩ	
Low side FET ON Resistance	R <sub>ONL</sub>	-	65	130	mΩ	
Reference Voltage						
FB threshold Voltage	V <sub>FB</sub>	0.788	0.800	0.812	V	
FB Input Current	I <sub>FB</sub>	-1	-	1	μA	
H <sup>3</sup> Reg Control						
ON Time	T <sub>ON</sub>	-	470	-	nsec	
Minimum OFF Time	TOFFMIN	200	450	-	nsec	
Soft Start / Output Discharge	. L					·
Soft Start Time	T <sub>SOFT</sub>	-	1.0	-	msec	
VOUT Discharge Current	I <sub>VOUT</sub>	3	6.6	-	mA	VOUT=1V, EN=0V, V <sub>REG</sub> =5V

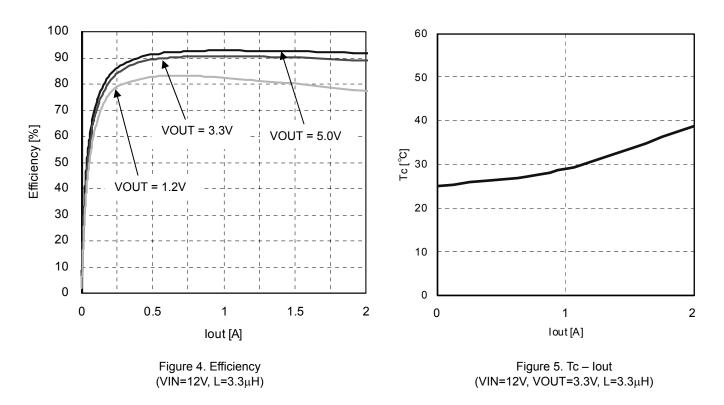
## Electrical Characteristics (Continued)

(Unless otherwise noted Ta=25°C, VIN=12V, EN=3V, VOUT=3.3V)

Parameter	Symbol	Limit			Unit	Condition	
Farameter	Symbol	Min	Тур	Max	Unit	Condition	
Over Current Protection							
Over Current Protection Current Limit	I <sub>OCP</sub>	2.5	3.5	6.0	А	*3	
SCP							
SCP Threshold Voltage	V <sub>SCP</sub>	0.48	0.56	0.64	V	$V_{FB}$ =0.8V $\rightarrow$ 0V	
SCP delay time	T <sub>SCP</sub>	-	1.0	-	msec		
OVP							
OVP Threshold Voltage	V <sub>OVP</sub>	0.86	0.96	1.06	V	$V_{FB}$ =0.8V $\rightarrow$ 2.0V	
OVP delay time	T <sub>OVP</sub>	-	1.0	-	msec		
UVLO							
VREG Threshold Voltage	$V_{\text{REG}\_\text{UVLO}}$	3.75	4.20	4.65	V	VREG: Sweep up	
VREG Hysteresis Voltage	$dV_{\text{REG}\_\text{UVLO}}$	100	160	220	mV	VREG: Sweep down	
Power Good							
V <sub>FB</sub> Power Good Low Voltage	$V_{FB_PL}$	0.61	0.68	0.75	V	$V_{FB}$ =0.8V $\rightarrow$ 0V	
V <sub>FB</sub> Power Good High Voltage	$V_{FB_PH}$	0.65	0.72	0.79	V	$V_{FB}=0V \rightarrow 0.8V$	

\*3 No tested on outgoing inspection.

## ●Typical Performance Curves (Unless otherwise noted Ta=25°C, VIN=12V)



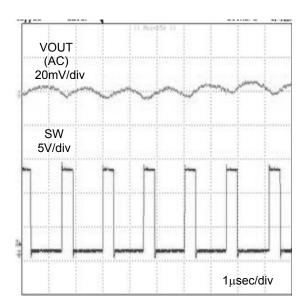


Figure 6. VOUT Ripple voltage (VIN=12V, VOUT=3.3V, L=3.3 $\mu$ H, COUT=44 $\mu$ F, Iout=0A)

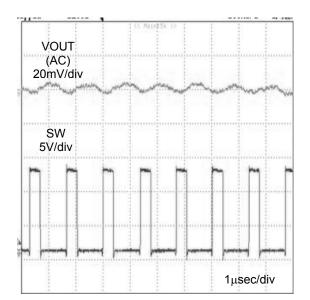
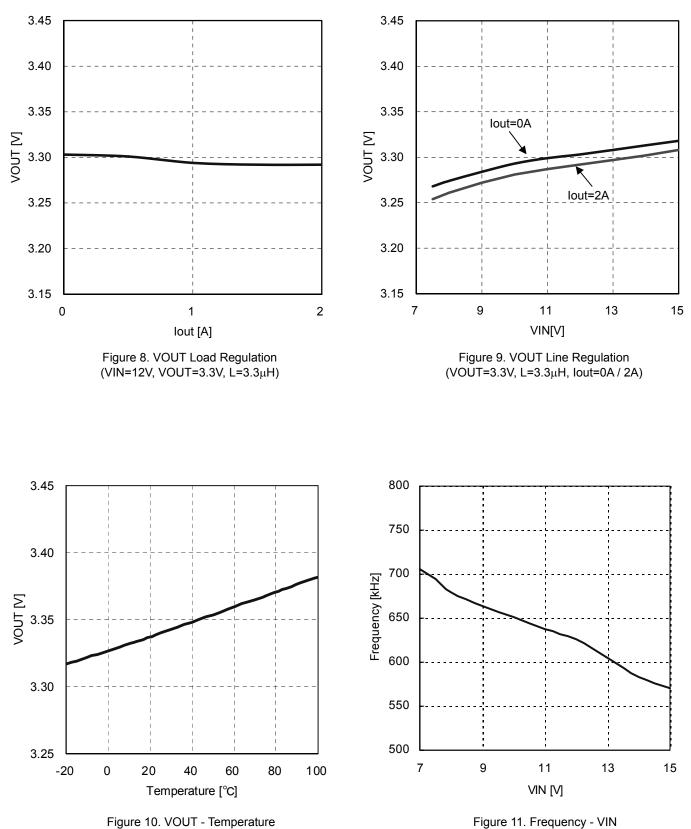


Figure 7. VOUT Ripple voltage (VIN=12V, VOUT=3.3V, L=3.3 $\mu$ H, COUT=44 $\mu$ F, Iout=2A)

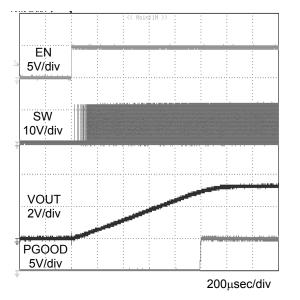
## ● Typical Performance Curves (Unless otherwise noted Ta=25°C, VIN=12V) (Continued)

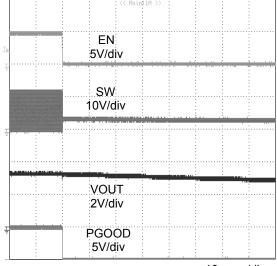


(VIN=12V, VOUT=3.3V, L=3.3μH, lout=0A)

(VIN=12V, VOUT=3.3V, L=3.3µH, lout=0A)

## ●Typical Performance Curves (Unless otherwise noted Ta=25°C, VIN=12V) (Continued)

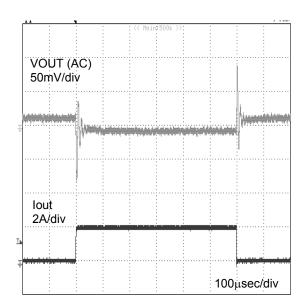




10msec/div

Figure 12. Start up with EN (VIN=12V, VOUT=3.3V, L=3.3 $\mu$ H, COUT=44 $\mu$ F, Iout=0A)

Figure 13. Power down with EN (VIN=12V, VOUT=3.3V, L=3.3 $\mu$ H, COUT=44 $\mu$ F, lout=0A)



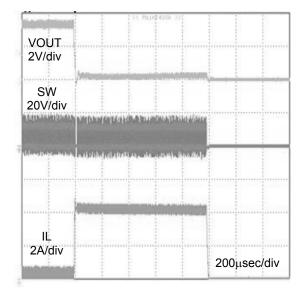


Figure 14. VOUT Transient Response (VIN=12V, VOUT=3.3V, L=3.3µH, COUT=44µF) Iout=0⇔2A (SR=1.0A/µsec) Figure 15. OCP function (VIN=12V, VOUT=3.3V, L=3.3 $\mu$ H, COUT=44 $\mu$ F) (VOUT is shorted to ground)

(1)

## **BD95821MUV**

#### Explanation of Operation

The BD95821MUV is a 1ch synchronous buck converter incorporating ROHM's proprietary H<sup>3</sup>Reg<sup>™</sup> CONTROLLA system. When VOUT drops due to a rapid load change, the system quickly restores VOUT by increasing the frequency.

## 1. H<sup>3</sup>Reg<sup>™</sup> System

1-1. Normal Operation

When FB falls below the threshold voltage (REF), a drop is detected, activating the H<sup>3</sup>Reg<sup>™</sup> CONTROLLA system.

Ton = 
$$\frac{V_{OUT}}{V_{IN}} \times \frac{1}{f}$$
 [sec]

HG (Gate of High side MOSFET) output is determined by the formula (1). LG (Gate of Low side MOSFET) output operates until FB voltage falls below REF voltage after HG becomes OFF. OFF time is restricted by MIN OFF Time (typ.:450nsec). Hence, BD95821MUV runs with a constant on-time by using the input and output voltage to set the internal on-time timer.

## 1-2. VOUT drops due to a rapid load change

When FB (VOUT) drops due to a rapid load change and the voltage remains below REF, the system quickly restores VOUT by shortening OFF time of HG (increasing the frequency), improving transient response as shown Figure 16 (b).

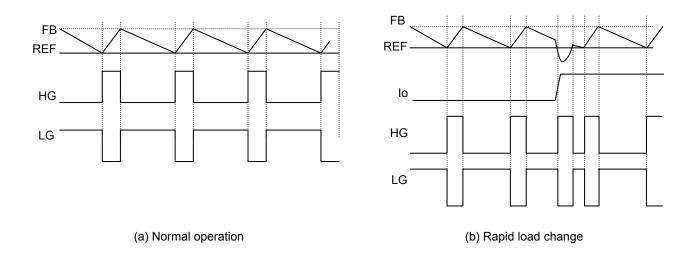


Figure 16. H<sup>3</sup>REG System

## **BD95821MUV**

#### Timing Chart

#### 1. Soft Start Function

Soft start is utilized when the EN pin is set high. Current control takes effect at startup, enabling a moderate "ramping start" on the output voltage. Soft start time is 1.0msec (typ). Rush current is determined via formula (2) below.

$$I_{IN} = \frac{C_{OUT} \times V_{OUT}}{1.0 \text{msec}} \qquad [A]$$

COUT: All capacitors connected with VOUT

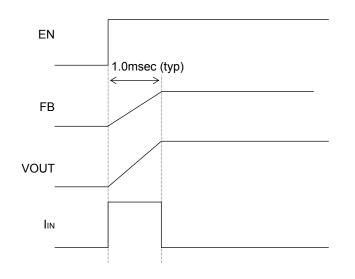


Figure 17. Soft Start Timing Chart

#### 2. Power Good Function

When FB voltage is more than 0.72V (90%), the integrated open-drain NMOS is set to OFF, and PGOOD outputs High due to pull-up register. If FB voltage falls below 0.68V (85%), PGOOD becomes Low.

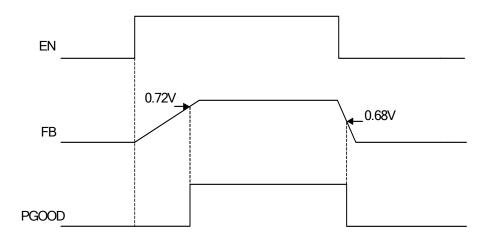


Figure 18. Power Good Timing Chart

#### Protection Operation

#### 1. OCP Operation

Normally, when FB voltage falls below REF voltage, HG becomes high. However, if the current through the inductor ( $I_L$ ) exceeds OCP current value ( $I_{OCP}$ ) during LG=ON, HG does not become high and  $I_L$  is restricted by  $I_{OCP}$ . When  $I_L$  falls down below  $I_{OCP}$ , HG is stricken by the pulse width of Ton decided by formula (1). As the result, the output voltage can decrease as the frequency and duty are changed.

When OCP is released in the state that the output has decreased by OCP operation, the output voltage might rise up due to high-speed load response. Also OFF Latch is operated when FB voltage becomes below the SCP setting voltage during 1msec (typ.) (Refer to 2-1).

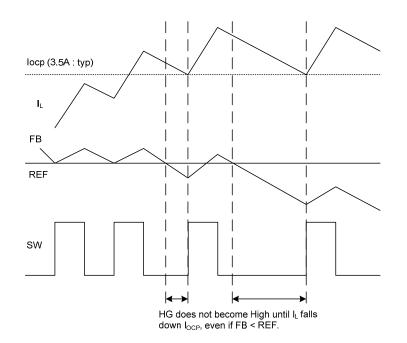


Figure 19. OCP Timing Chart

## 2. SCP Operation / OVP Operation (OFF Latch)

#### 2-1. SCP Operation

SCP monitors FB voltage. When FB falls below 0.56V, after 1msec (typ.) later, the short circuit protection (SCP) operates, turning the high side MOSFET and low side MOSFET OFF, and performs OFF latch operation.

#### 2-2. OVP Operation

OVP monitors FB voltage. When FB exceeds 0.96V, after 1msec (typ.) later, the output over voltage protection (OVP) operates, turning the high side FET OFF and the low side FET ON, and performs OFF latch operation.

#### 2-3. Recovery from OFF Latch mode

Off latch is released by EN=OFF or UVLO operation, and then it returns to standard operation.

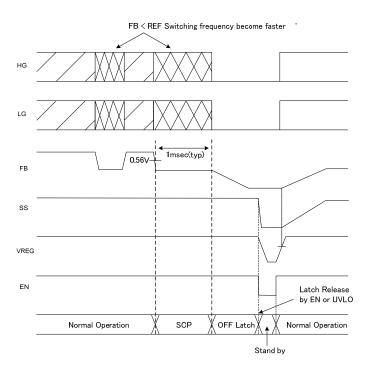
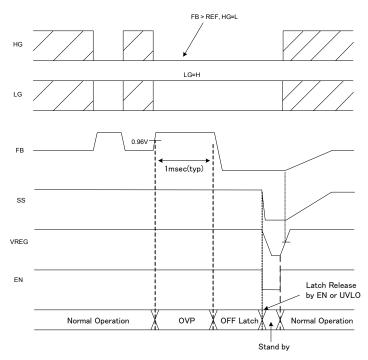


Figure 20. SCP Timing Chart





#### 3. TSD Operation (Self Recovery)

TSD is self-activating. If the junction temperature exceeds Tj =  $175^{\circ}$ C, and HG, LG, PGOOD, and SS become Low. The IC becomes standby when TSD operating.

When Tj falls below 150°C, it returns to standard operation.

#### 4. UVLO Operation

UVLO operates when VREG voltage falls below 4.05V, ad HG, LG, PGOOD and SS become Low.

The IC becomes standby when UVLO operating.

UVLO is released when VREG goes up to 4.2V, and starts standard operation

#### Selection of Components Externally Connected

1. Output LC Filter Selection (Buck Converter)

1-1. Inductor (L) Selection

The Output LC filter is required to supply constant current to the output load. A larger value inductance at this filter results in less inductor ripple current ( $\Delta I_L$ ) and less output ripple voltage. However, the larger value inductors tend to have less fast load transient-response, a larger physical size, a lower saturation current and higher series resistance. A smaller value inductance has almost opposite characteristics above.

The recommended inductor values are shown in Table 1(Refer to page 18).

The value of  $\Delta I_L$  is shown as formula (3).

$$\Delta I_{L} = \frac{\left(V_{IN} - V_{OUT}\right) \times V_{OUT}}{L \times f \times V_{IN}} \qquad [A]$$

For example, with VIN = 12 V, VOUT = 3.3 V, L =  $3.3 \mu\text{H}$  and the switching frequency f = 600 kHz, the calculated ripple current  $\angle$ IL is 1.2A.

Then, the inductor saturation current must be larger than the sum of the maximum output current (IOUTMAX) and 1/2 of the inductor ripple current ( $\Delta$ IL / 2). A larger current than the inductor's saturation current will cause magnetic saturation in the inductor, and decrease efficiency. When selecting an inductor, be sure to allow enough margins to assure that peak current does not exceed the inductor's saturation current value.

\* To minimize loss of inductor and improve efficiency, choose a inductor with a low resistance (DCR, ACR).

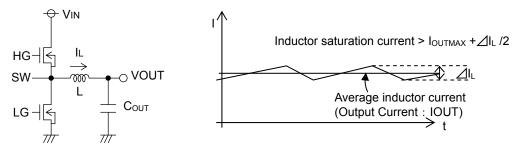


Figure 22. Inductor Ripple Current

1-2. Output Capacitor (C<sub>OUT</sub>) Selection

Output Capacitor ( $C_{OUT}$ ) has a considerable influence on output voltage regulation due to a rapid load change and smoothing output ripple voltage. Determine the capacitor by considering the value of capacity, the equivalent series resistance, and equivalent series inductance. Also, make sure the capacitor's voltage rating is high enough for the set output voltage (including ripple).

Output ripple voltage is determined as in formula (4) below.

$$\Delta \text{VOUT} = \Delta \text{I}_{\text{L}} / (8 \times \text{C}_{\text{OUT}} \times \text{f}) + \text{ESR} \times \Delta \text{I}_{\text{L}} + \text{ESL} \times \Delta \text{I}_{\text{L}} / \text{Ton} \qquad [V]$$
(4)

(ΔIL Output ripple current、ESR: Equivalent series resistance、ESL: Equivalent series inductance)

Also, give consideration to the conditions in formula (5) below for output capacitance, bearing in mind that output rise time must be established within the fixed soft start time. As output capacitance, bypass capacitor will be also connected to output load side ( $C_{EXT}$ , Figure 23). Please set the over current detection value with regards to these capacitance.

$$C_{OUT} \leq \frac{1 \text{msec } \times (I_{OCP} - I_{OUT})}{V_{OUT}} \qquad [F]$$
(5)

(I<sub>OCP</sub>: OCP Current Limit, I<sub>OUT</sub>: Output Current)

Note: an improper output capacitor may cause startup malfunctions.

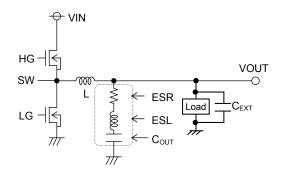


Figure 23. Output Capacitor

current I<sub>RMS</sub> is given in equation (6) as below.

Where VIN =2 × VOUT, IRMS =  $\frac{100T}{2}$ 

 $I_{RMS} = I_{OUT} \times \frac{\sqrt{V_{OUT} \times (V_{IN} - V_{OUT})}}{V_{IN}}$ 

In order to prevent transient spikes in voltage, the input capacitor should have a low

enough ESR resistance to fully support a large ripple current. The formula for ripple

[A]

A low ESR capacitor is recommended to reduce ESR loss and improve efficiency.

(6)

#### 2. Input Capacitor (CIN) Selection

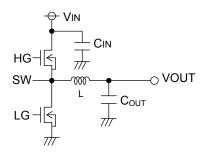


Figure 24. Input Capacitor

3. Output Voltage Setting

The IC controls output voltage as  $REF \Rightarrow V_{FB}$ .

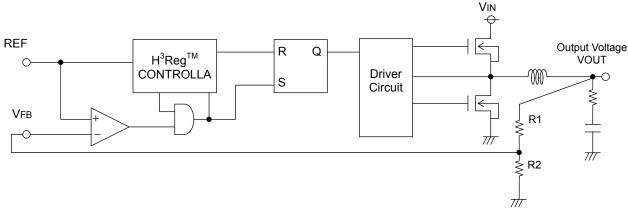
However, the actual output voltage will also reflect the average ripple voltage value.

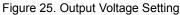
VIN

The output voltage is set with a resistor divider from the output node to the FB pin. The formula for output voltage is given in (7) below:

Output Voltage = 
$$\frac{R1+R2}{R2}$$
 × REF + $\Delta$ VOUT [V] (7)  
REF = VFB(TYP 0.8V) + 0.02 - (ON DUTY × 0.05) [V] (8)  
ON DUTY =  $\frac{VOUT}{VC}$  (9)

Please refer to eq. (4) regarding 
$$\Delta VOUT$$
.





#### 4. Relationship between Output Voltage and ONTIME

BD95821MUV is a synchronous buck converter controlling constant ONTIME. The ONTIME (Ton) depends on the output voltage settings, as described by the formula (10).

Ton = 
$$1770 \times \frac{V_{OUT}}{V_{IN}} - \frac{610}{V_{IN}} + 55$$
 [nsec] (10)

The frequency of the application condition is determined by the formula (11) using the above Ton.

Frequency = 
$$\frac{\text{VOUT}}{\text{V}_{\text{IN}}} \times \frac{1}{\text{Ton}}$$
 [kHz] (11)

However with actual applications, there exists a rising and falling time of the SW due to the gate capacitance of the integrated MOSFET and the switching speed, which may vary the above parameters. Therefore please also verify those parameters experimentally.

#### 5. Relationship between Output Current and Frequency

BD95821MUV is a constant ontime type of switching regulator. When the output current increases, the switching loss of the inductor, MOSFET, and output capacitor also increases. Hence the switching frequency speeds up. The loss of the inductor, MOSFET, and output capacitor is determined as below.

(1) Loss of Inductor = 
$$IOUT^2 \times DCR$$
  
(2) Loss of MOSFET (High Side) =  $IOUT^2 \times R_{ONH} \times \frac{VOUT}{VIN}$   
(3) Loss of MOSFET (Low Side) =  $IOUT^2 \times R_{ONL} \times (1 - \frac{VOUT}{VIN})$   
(4) Loss of Output Capacitor =  $IOUT^2 \times ESR$ 

(DCR : Inductor Equivalent series resistance, R<sub>ONH</sub> : On resistance of High-side MOSFET, R<sub>ONL</sub> : On resistance of Low-side MOSFET, ESR :COUT Equivalent series resistance)

Taking the above losses into the frequency equation, then T (=1/Freq) becomes

$$T (=1/Freq) = \frac{VIN \times IOUT \times Ton}{VOUT \times IOUT + (1 + (2 + (3 + (4))))}$$
 [nsec] (12)

However since the parasitic resistance of the PCB layout pattern exists in actual applications and affects the parameter, please also verify experimentally.

#### ●PCB Layout Guide

Two high pulsing current flowing loops exist in the buck regulator system.

The first loop, when FET is ON, starts from the input capacitors, to the VIN terminal, to the SW terminal, to the inductor, to the output capacitors, and then returns to the input capacitor through GND.

The second loop, when FET is OFF, starts from the low FET, to the inductor, to the output capacitor, and then returns to the low FET through GND.

To reduce the noise and improve the efficiency, please minimize these two loop area.

Especially input capacitor and output capacitor should be connected to GND (PGND) plain.

PCB Layout may affect the thermal performance, noise and efficiency greatly. So please take extra care when designing PCB Layout patterns.

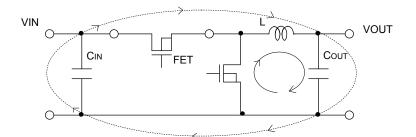


Figure 26. Current loop Buck regulator system

- The thermal Pad on the back side of IC has the great thermal conduction to the chip. So using the GND plain as broad and wide as possible can help thermal dissipation. And a lot of thermal via for helping the spread of heat to the different layer is also effective.
- The input capacitors should be connected to PGND as close as possible to the VIN terminal.
- The inductor and the output capacitors should be placed close to SW pin as much as possible.

#### List of Evaluation Board Components

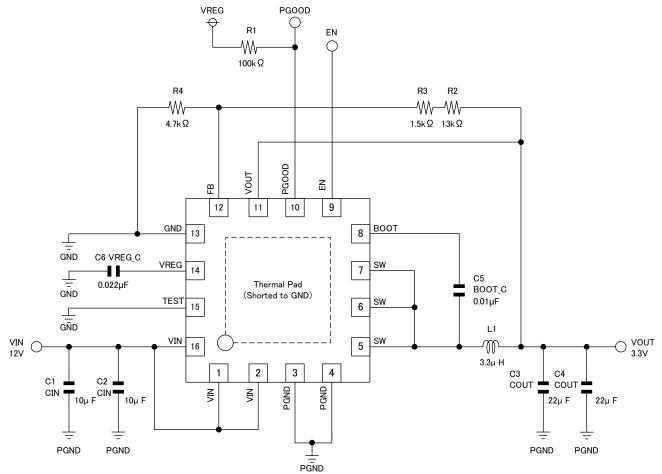


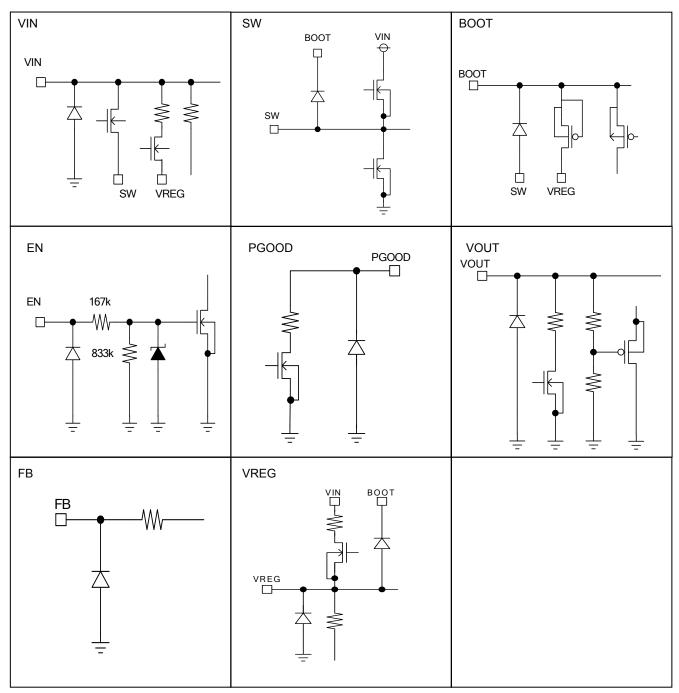
Figure 27. Typical Application Circuit (VOUT=3.3V)

Symbol	Part	Value	Manufacture	Series
	0-11		ТОКО	FDVC0630 Series
L1	Coil	*	TDK	SPM6530 Series
CIN (C1, C2)	Ceramic capacitor	10µF / 25V	Murata	GRM31CR71E16KA12
COUT (C3, C4)	Ceramic capacitor	22µF / 16V	Murata	GRM31CB31C226ME15
BOOT_C (C5)	Ceramic capacitor	0.01µF / 50V	Murata	GRM18 Series
R1	Resistance	100k Ω	Rohm	MCR03 Series
R2	Resistance	*	Rohm	MCR03 Series
R3	Resistance	*	Rohm	MCR03 Series
R4	Resistance	*	Rohm	MCR03 Series
VREG_C (C6)	Ceramic capacitor	0.022µF / 50V	Murata	GRM18 Series

*	VOUT	R2	R3	R4	L1
	1.0V	<b>360</b> Ω	130 <i>Ω</i>	2.2kΩ	1.5µH
	1.2V	2kΩ	220 Ω	4.7kΩ	1.5µH
	1.8V	5.6kΩ	110 <i>Ω</i>	4.7kΩ	2.2μH
	3.3V	13kΩ	1.5kΩ	4.7kΩ	3.3µH
	5.0V	24kΩ	680 Ω	4.7kΩ	3.3µH

The above components list is an example. Please check actual circuit characteristics on the application carefully before use.

### ●I/O Equivalence circuit



#### Operational Notes

(1) Absolute Maximum Ratings

Use of the IC in excess of absolute maximum ratings may result in damage to the IC. Assumptions should not be made regarding the state of the IC (e.g., short mode or open mode) when such damage is suffered. If operational values are expected to exceed the maximum ratings for the device, consider adding protective circuitry (such as fuses) to eliminate the risk of damaging the IC.

(2) GND voltage

The potential of the GND, PGND pin must be the minimum potential in the system in all operating conditions.

(3) Thermal design

Use a thermal design that allows for a sufficient margin for power dissipation (Pd) under actual operating conditions

(4) Inter-pin Shorts and Mounting Errors

Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Shorts between output pins or between output pins and the power supply and GND pins caused by poor soldering or foreign objects may result in damage to the IC.

- (5) Operation in Strong Electromagnetic Fields Using this product in strong electromagnetic fields may cause IC malfunction. Caution should be exercised in applications where strong electromagnetic fields may be present.
- (6) ASO (Area of Safe Operation)

When using the IC, ensure that operating conditions do not exceed absolute maximum ratings or ASO of the output transistors.

(7) Testing on application boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from a jig or fixture during the evaluation process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

(8) Electrical Characteristics

The electrical characteristics indicated in this datasheet may change upon the conditions of temperature, supply voltage, and external components. Please validate/verify your design at the worst case conditions.

- (9) Not of a radiation-resistant design.
- (10) Back Electromotive Force

If a large inductive load is connected at the output pin that might cause introducing back electromotive force at the start up and at the output disable, please insert protection diodes.

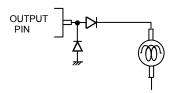


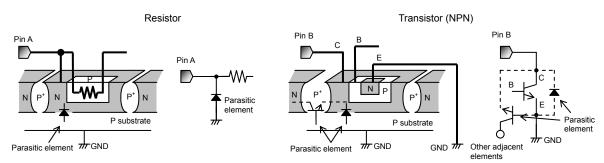
Figure 28. Back Electromotive Force

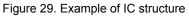
(11) Regarding input pins of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. PN junctions are formed at the intersection of these P layers with the N layers of other elements, creating parasitic diodes and/or transistors. For example (refer to the figure below):

- · When GND > Pin A and GND > Pin B, the PN junction operates as a parasitic diode
- When GND > Pin B, the PN junction operates as a parasitic transistor

Parasitic diodes occur inevitably in the structure of the IC, and the operation of these parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Accordingly, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.





(12) Ground Wiring Pattern

When using both small-signal and large-current GND traces, the two ground traces should be routed separately but connected to a single ground potential within the application in order to avoid variations in the small-signal ground caused by large currents. Also ensure that the GND traces of external components do not cause variations on GND voltage.

(13) Operating Condition

The electrical characteristics indicated in this datasheet are not guaranteed for the whole operational and temperature ranges, however these characteristics do not significantly fluctuate within the operational and temperature ranges.

#### (14) Thermal shutdown (TSD) circuit

The IC incorporates a built-in thermal shutdown circuit, which is designed to turn the IC off completely in the event of thermal overload. It is not designed to protect the IC from damage or guarantee its operation. ICs should not be used after this function has activated, or in applications where the operation of this circuit is assumed. If the thermal shutdown is activated while the load current exists, the output may possibly be latched off at the release of the thermal shutdown.

TSD ON Temp.[°C] (typ.)	Hysteresis Temp[°C] (typ.)
175	25

#### (15) Heat Sink (FIN)

The heat sink (FIN) is connected to the substrate. Please connect it to GND.

#### Thermal Derating Curves

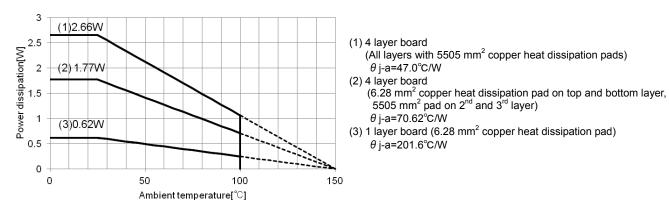
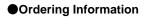
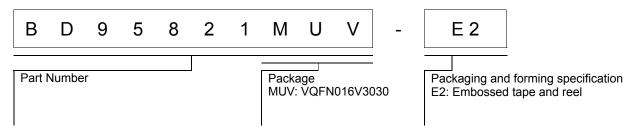


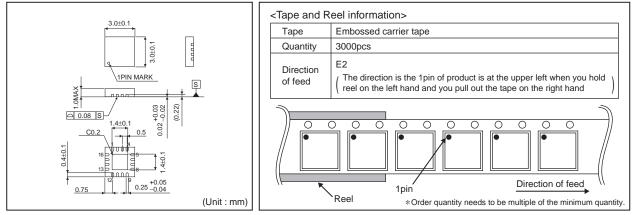
Figure 30. Thermal derating curve (VQFN016V3030)



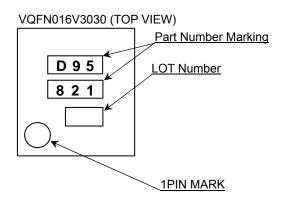


#### Physical Dimension Tape and Reel Information

#### VQFN016V3030



#### Marking Diagram



## **BD95821MUV**

#### Revision History

Date	Revision	Changes
6.Aug.2012	001	New Release
24.Aug.2012	002	Revised the General Description
18.Mar.2013	003	Revised the General Description

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CLASSⅣ		CLASSⅢ	

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